CE65H900TOEI

CoreGaN 650V GaN HEMT

Description

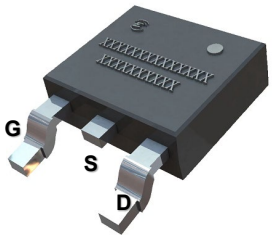
The CE65H900TOEI Series 650V, 900mΩ gallium nitride (GaN) FETs are normally-off devices.

Corenergy GaN FETs offer better efficiency through lower gate charge, faster switching speeds, and lower dynamic on-resistance, delivering significant advantages over traditional silicon (Si) devices.

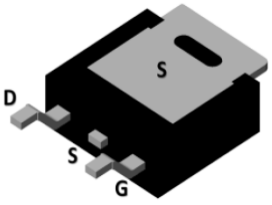
Corenergy is a leading-edge wide band gap supplier with world-class innovation .

Ordering Information

Part Number	Package	Package Configuration
CE65H900TOEI	TO252	Source



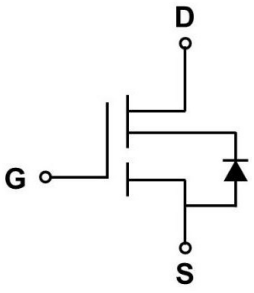
Top



Bottom

Application

- Adapter
- Renewable energy
- Telecom and data-com
- Servo motors
- Industrial
- Automotive



Circuit Symbol

General Features

Easy to drive—compatible with standard gate drivers

Low conduction and switching losses

RoHS compliant and Halogen-free

Benefits

Increased efficiency through fast switching

Increased power density

Reduced system size and weight

Features

BV_{DSS}	R_{DSON}	I_{DS}	Q_G
650V	900 mΩ	3A	4.6nC

CorEnergy®

CE65H900TOEI

Absolute Maximum Ratings

T_c=25°C unless otherwise stated

Symbol	Parameter		Limit value	Unit
V_{DSS}	Drain to source voltage (T_J = -55°C to 150°C)		650	V
$V_{(TR)DSS}$	Drain to source voltage-transient [a]		800	
V_{GSS}	Gate to source voltage		-20~+20	
I_D	Continuous drain current @T_C=25°C [b]		3	A
	Continuous drain current @T_C=125°C [b]		1.4	
I_{DM}	Pulse drain current (pulse width: 10μs)		5	A
P_D	Maximum power dissipation @ T_C=25°C		21	W
T_C	Operating temperature	Case	-55~150	°C
T_J		Junction	-55~150	°C
T_S	Storage temperature		-55~150	°C

a. In off-state, spike duty cycle D<0.01, spike duration <1μs

b. For increased stability at high current operation

Thermal Resistance

Symbol	Parameter	Limit value	Unit
$R_{\theta JC}$	Junction-to-case	6	°C /W

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Electrical Parameters

T_j=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics						
$V_{(BL)DSS}$	Drain-source voltage	650	-	-	V	V_{GS}= 0V
$V_{GS(th)}$	Gate threshold voltage	3.3	3.9	4.5	V	V_{DS}=1V, I_{DS}=1mA
$\triangle V_{GS(th)}/T_J$	Gate threshold voltage temperature coefficient	-	-7	-	mV/°C	
$R_{DS(on)}$	Drain-source on-Resistance	-	900	1080	mΩ	V_{GS}=10V, I_D=1A, T_J=25°C
		-	1900	-		V_{GS}=10V, I_D=1A, T_J=150°C
I_{DSS}	Drain-to-source leakage current	-	1	10	μA	V_{DS}=650V, V_{GS}= 0V, T_J=25°C
		-	5	100		V_{DS}=650V, V_{GS}= 0V, T_J=150°C
I_{GSS}	Gate-to-source forward leakage current	-	-	±100	nA	V_{GS}=±20V
C_{ISS}	Input capacitance	-	330	-	pF	V_{GS}=0V, V_{DS}=400V, f=1MHz
C_{OSS}	Output capacitance	-	9.2	-		
C_{RSS}	Reverse capacitance	-	3.8	-		
Q_G	Total gate charge	-	4.6	-	nC	V_{DS}=400V, V_{GS}=0V to 10V, I_D=1A
Q_{GS}	Gate-source charge	-	1.7	-		
Q_{GD}	Gate-drain charge	-	0.7	-		
Q_{OSS}	Output charge	-	12	-	nC	V_{GS}=0V, V_{DS}=0V to 400V, f=1MHz
$t_{D(on)}$	Turn-on delay	-	3.2	-	ns	V_{DS}=400V, V_{GS}=0V to 10V, I_D=2.1A, $R_{G-on(ext)}$=6.8Ω, $R_{G-off(ext)}$=2.2Ω, L=250μH
t_R	Rise time	-	5.5	-		
$t_{D(off)}$	Turn-off delay	-	7.4	-		
t_F	Fall time	-	27	-		

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Electrical Parameters

T_j=25°C unless otherwise stated

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
Reverse Device Characteristics						
V_{SD}	Source-Drain reverse voltage	-	3.1	-	V	V_{GS}=0V, I_{SD}=2.5A
t_{RR}	Reverse recovery time	-	14	-	ns	I_F=2.5A, V_{DD}=400V, dI_F/dt=165A/μs
Q_{RR}	Reverse recovery charge	-	6.5	-	nC	

Typical Characteristics

T_J=25°C unless otherwise stated

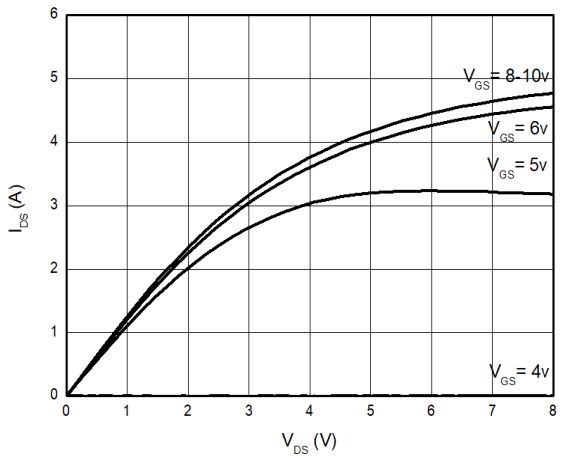

Figure 1. Typical Output Characteristics T_J=25°C

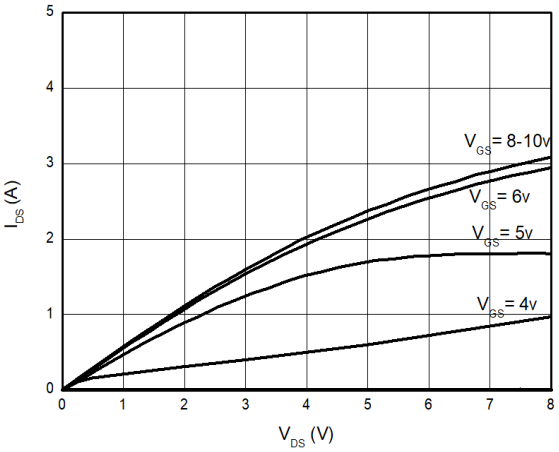

Figure 2. Typical Output Characteristics T_J=125°C

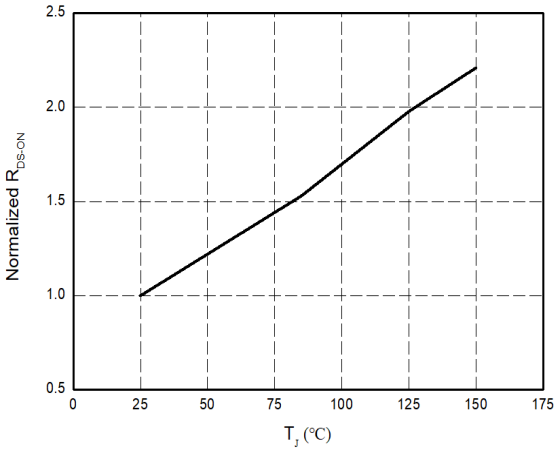

Figure 3. Normalized On-resistance

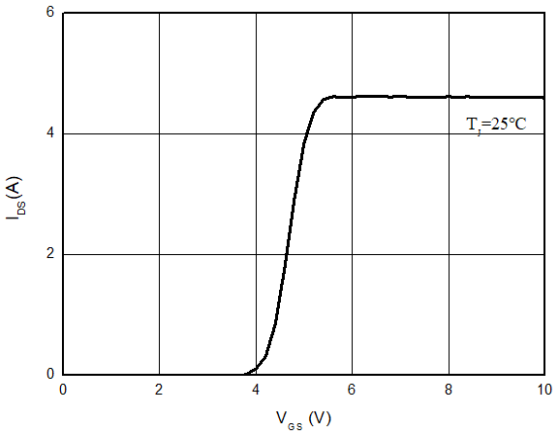

Figure 4. Typical Transfer Characteristics T_J=25°C

Typical Characteristics

T_j=25°C unless otherwise stated

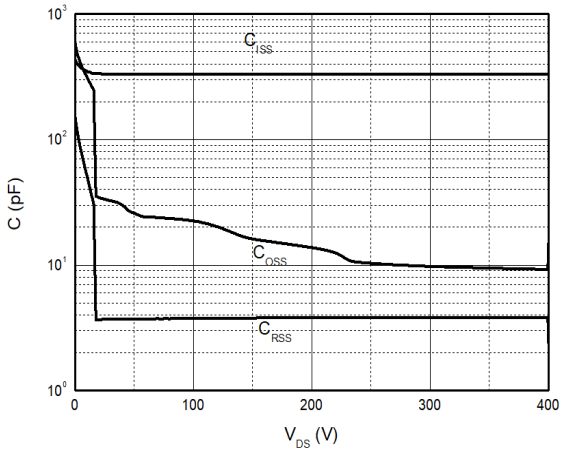

Figure 5. Typical Capacitance (f=1MHz)

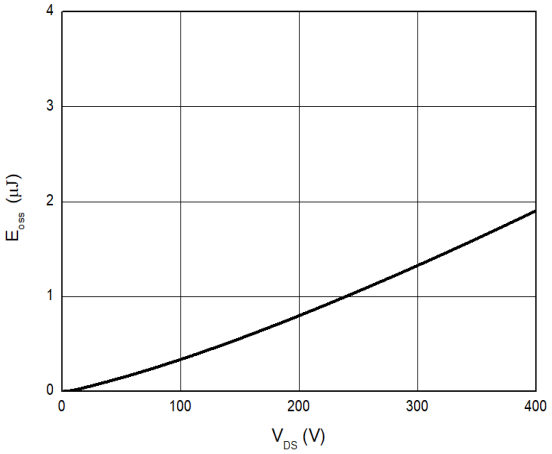

Figure 6. Typical C_{OSS} Stored Energy

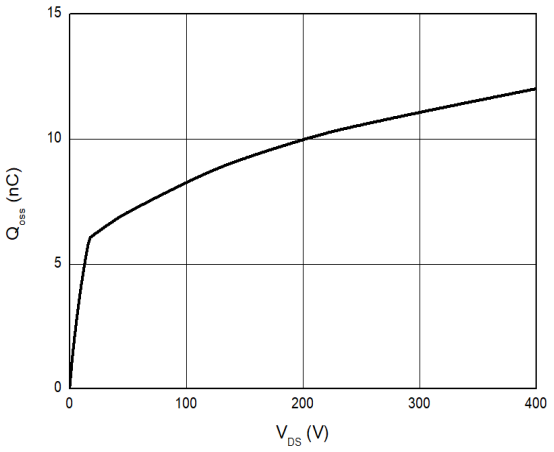

Figure 7. Typical Q_{OSS}

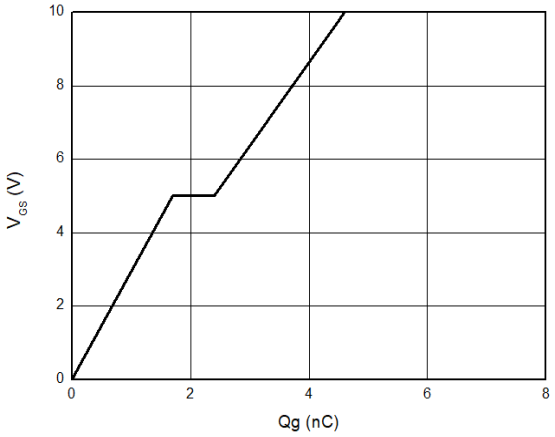

Figure 8. Typical Gate Charge (V_{DS}=400V, I_D=1A)

Typical Characteristics

T_j=25°C unless otherwise stated

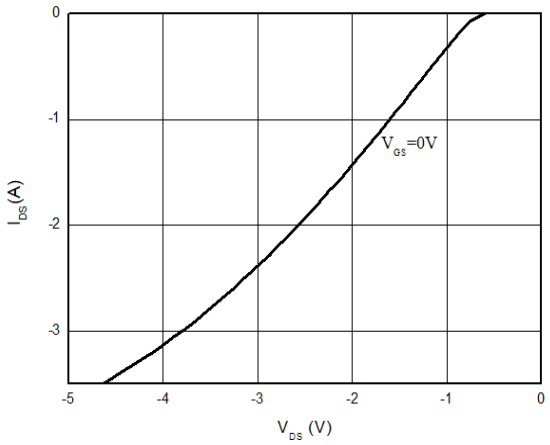

Figure 9. Channel Reverse Characteristics T_J=25°C

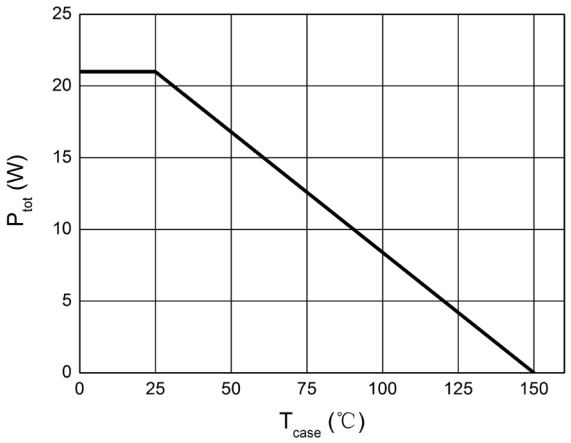

Figure 10. Power Dissipation

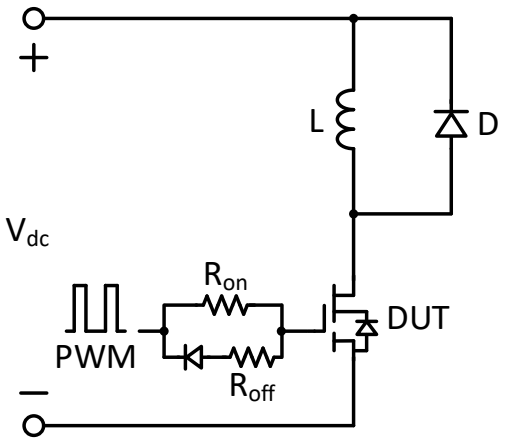

Figure 11 Switching times with inductive load

V_{DS}=400V, V_{GS}=0V to 10V, I_D=2.1A,
$R_{G-on(ext)}$=6.8Ω, $R_{G-off(ext)}$=2.2Ω, L=250μH

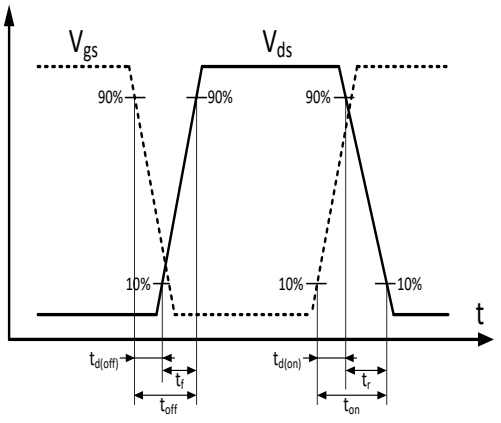

Figure 12. Switching times with waveform

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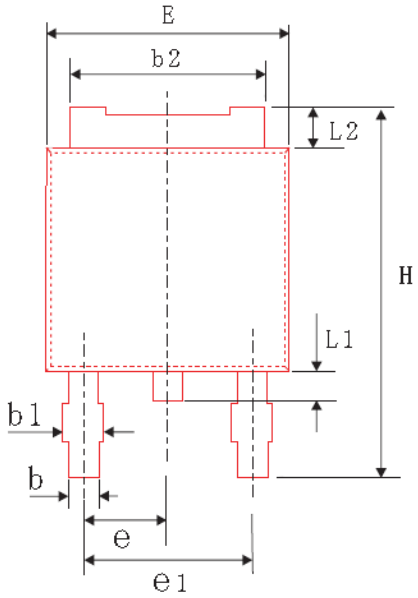
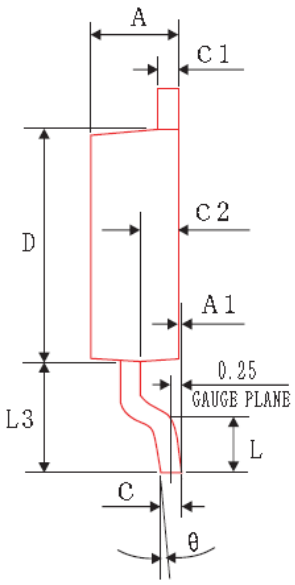
PACKAGE DIMENSIONS

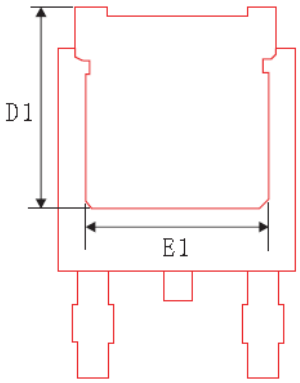
TO252-2L



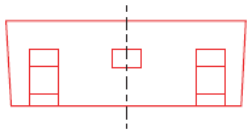
TOP VIEW



SIDE VIEW



BOTTOM VIEW



SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE-mm)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	0.05	0.10
b	0.762	0.812	0.862
b1	——	——	1.10
b2	5.23	5.33	5.43
c	0.458	0.508	0.558
c1	0.458	0.508	0.558
c2	0.80	1.00	1.20
D	6.00	6.10	6.20
D1	5.25	5.45	5.65
H	10.00	10.10	10.20
E	6.50	6.60	6.70
E1	4.75	4.85	4.95
e1	4.37	4.57	4.77
L	——	——	1.45
L1	0.60	0.75	0.90
L2	0.90	1.10	1.30
L3	2.80	3.00	3.20
θ	0°	4°	8°
e	2.285 BSC		

CE65H900TOEI

Revision history

Major changes since the last revision

Revision	Date	Description of changes
1.0	2022-02-28	Initial release
2.0	2023-10-30	Enrich dynamic specification curves
3.0	2023-12-25	Update dynamic parameters